METHOD AND STRUCTURE FOR IMPROVING CMOS DEVICE RELIABILITY USING COMBINATIONS OF INSULATING MATERIALS

ABSTRACT

A method for improving hot carrier effects in complementary metal oxide semiconductor (CMOS) devices (102, 104) includes forming a first configuration of insulating material (116, 118) over a first group of the CMOS devices (102), and forming a second configuration of insulating material (122) over a second group of the CMOS devices (104). The first and said second configurations (116, 118, 122) of insulating material are formed subsequent to a silicidation of the CMOS devices (102, 104) and prior to formation of a first interlevel (ILD) dielectric material over the CMOS devices (102, 104).

Fig. 8.



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